

**IN THE CLAIMS**

Cancel claims 13-39 and 54-57 without prejudice or disclaimer.

1. (Original) A semiconductor device comprising:

a seal member formed of an insulating resin;

a tab whose back side is exposed to a mounting surface of the seal member, the tab having, on a surface thereof opposite to the back side, a semiconductor element fixing area and wire connection areas;

tab suspension leads exposed to the mounting surface of the seal member and contiguous to the tab;

a plurality of leads whose back sides are exposed to the mounting surface of the seal member;

a semiconductor element positioned within the seal member and fixed through an adhesive onto the semiconductor element fixing area on the surface of the tab in such a manner that a back side thereof is opposed to the tab surface;

a plurality of electrodes formed on a main surface of the semiconductor element;

electrically conductive wires for electrically connecting the plural electrodes and surfaces of the leads with each other; and

electrically conductive wires for electrically connecting the electrodes on the semiconductor element and the wire connection areas on the tab with each other;

wherein the tab is formed larger than the semiconductor element so that outer peripheral edges of the tab are positioned outside outer peripheral edges of the semiconductor element; and

wherein a groove is formed in the surface of the tab so as to be positioned between the semiconductor element fixing area and the wire connection areas.

2. (Original) A semiconductor device according to claim 1, wherein the groove surrounds a whole circumference of the semiconductor element fixing area.

3. (Original) A semiconductor device according to claim 1, wherein the adhesive is not applied to the wire connection areas on the tab.

4. (Original) A semiconductor device according to claim 1, wherein a plating film is formed selectively on the wire connection areas of the tab and the surfaces of the leads, and the wires are connected onto the plating film.

5. (Original) A semiconductor device according to claim 1, wherein an area of the surface of the tab is larger than that of the back side of the tab.

6. (Original) A semiconductor device according to claim 5, wherein the tab has a section which is in the shape of an inverted trapezoid.

7. (Original) A semiconductor device according to claim 1, wherein the adhesive is applied also to the interior of the groove and the semiconductor element is larger than the semiconductor element fixing area and is fixed also onto the groove through the adhesive.

8. (Original) A semiconductor device according to claim 1, wherein the groove is selectively formed correspondingly to areas where the wires are connected.

9. (Original) A semiconductor device according to claim 1, wherein the tab is quadrangular and the groove is formed selectively in a mutually independent manner without being formed at four corners of the tab.

10. (Original) A semiconductor device according to claim 1, wherein the tab is quadrangular and the groove is formed selectively in a mutually independent manner along sides of the quadrangle.

11. (Original) A semiconductor device according to claim 1, wherein grooves are formed in the surfaces of the leads respectively and the wires are connected at positions closer to the semiconductor element with respect to the grooves formed in the surfaces of the leads.

12. (Original) A semiconductor device according to claim 1, wherein the grooves are formed by pressing work.

13-39. (Canceled)

40. (Original) A semiconductor device comprising:  
a seal member formed of an insulating resin;  
a tab whose back side is exposed to a mounting surface of the seal member, the tab having, on a surface thereof opposite to the back side, a semiconductor element fixing area and wire connection areas;

tab suspension leads exposed to the mounting surface of the seal member and contiguous to the tab;

a plurality of leads whose back sides are exposed to the mounting surface of the seal member;

a semiconductor element positioned within the seal member and fixed through an adhesive onto the semiconductor element fixing area on the surface of the tab in such a manner that a back side thereof is opposed to the tab surface;

a plurality of electrodes formed on a main surface of the semiconductor element;

electrically conductive wires for electrically connecting the plural electrodes and surfaces of the leads with each other; and

electrically conductive wires for electrically connecting the electrodes on the semiconductor element and the wire connection areas on the tab with each other,

wherein the tab is formed larger than the semiconductor element so that outer peripheral edges of the tab are positioned outside outer peripheral edges of the semiconductor element; and

wherein a slit which pierces the tab is formed partially in the tab portion positioned between the semiconductor element fixing area and the wire connection areas.

41. (Original) A semiconductor device according to claim 40, wherein the semiconductor element fixing area is quadrangular and the slit formed as a single slit or as a row of plural intermittent slits along sides of the semiconductor element fixing area.

42. (Original) A semiconductor device according to claim 41, wherein from the slit toward an outer peripheral edge of the tab there is formed one or plural slits so as not to reach an edge of the tab.

43. (Original) A semiconductor device according to claim 42, wherein the wire connection areas are partially surrounded with the slit and the one or plural slits extending from the slit.

44. (Original) A semiconductor device according to claim 41, wherein from the slit toward an outer peripheral edge of the tab there is formed one or plural grooves.

45. (Original) A semiconductor device according to claim 44, wherein the wire connection areas are partially

surrounded with the slit and the one or plural grooves extending from the slit.

46. (Original) A semiconductor device according to claim 40, wherein the adhesive is not applied to the wire connection areas on the tab.

47. (Original) A semiconductor device according to claim 40, wherein a plating film is selectively formed on surfaces of the wire connection areas of the tab and surfaces of the leads, and the wires are connected onto the plating film.

48. (Original) A semiconductor device according to claim 40, wherein an area of the surface of the tab is larger than that of the back side of the tab.

49. (Original) A semiconductor device according to claim 40, wherein the tab is quadrangular and the slit is formed selectively in a mutually independent manner without being formed at four corners of the tab.

50. (Original) A semiconductor device according to claim 40, wherein grooves are formed in the surfaces of the leads respectively and the wires are connected at positions closer to the semiconductor element with respect to the grooves formed in the surfaces of the leads.

51. (Original) A semiconductor device according to claim 40, wherein the tab, the tab suspension leads, and the plural leads are all formed of one and same metallic material.

52. (Original) A semiconductor device according to claim 40, wherein the plural leads are arranged around the tab and a space between the leads and the tab is filled with the seal member.

53. (Original) A semiconductor device according to claim 40, wherein the wire connection areas on the tab are electrically connected through a plurality of wires to a plurality of electrodes as voltage supply electrodes for the semiconductor element.

54-57. (Canceled)